

Application No. 10/658,772
Amendment dated October 3, 2005
After Final Office Action of August 17, 2005

Docket No.: 0941-0835P

AMENDMENTS TO THE CLAIMS

1-15. (Cancelled)

16. (Original) A semiconductor device comprising:

a substrate;

an internal circuit formed on the substrate, comprising:

a first gate formed on the substrate; and

a first source and drain region formed in the substrate and respectively on both sides of the first gate; and

an electrostatic discharge protection circuit formed on the substrate, comprising:

a second gate formed on the substrate; and

a second source and drain region formed in the substrate and respectively on both sides of the second gate; and

a first and second lightly doped region formed in the substrate, wherein the first lightly doped region surrounds the first drain region, the second lightly doped region is only disposed between the second gate and the second drain region, and the first and second lightly doped region both have a depth greater than that of the first and second drain region.

17. (Original) The semiconductor device as claimed in claim 16, wherein all the source and drain regions are N⁺ doped regions.

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18. (Original) The semiconductor device as claimed in claim 16, wherein all the source and drain regions are P⁺ doped regions.

19. (Original) The semiconductor device as claimed in claim 16, wherein the first and second lightly doped regions are N⁻ type ESD implantation regions.

20. (Original) The semiconductor device as claimed in claim 16, wherein the first and second lightly doped regions are P⁻ type ESD implantation regions.

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